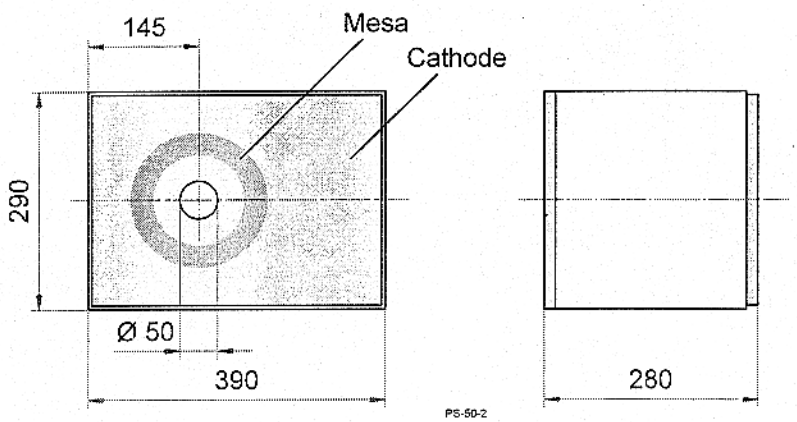
Point-source LED chip (∅ 50 µm) ELC-870-29-2

Preliminary data

Radiation	Type	Technology	Electrodes
Infrared	ELC-870-29-2	AlGaAs/GaAs	N (cathode) up

Outline (dimensions in microns)



Maximum Ratings

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Value	Unit
Forward current (DC)		I_F	50	mA
Peak forward current	($t_P \leq 50$ µs, $t_P/T=1/2$)	I_{FM}	100	mA

Optical and Electrical Characteristics

T_{amb} = 25°C, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 20 mA	V_F		1.40		V
Forward voltage	I_F = 50 mA	V_F		1.50		V
Reverse voltage	I_R=100 µA	V_R	5			V
Radiant power	I_F = 20 mA	Φ_e		0.4		mW
Radiant power	I_F = 50 mA	Φ_e		0.9		mW
Radiant intensity	I_F = 50 mA	I_e		0.4		mW/sr
Peak wavelength	I_F = 50 mA	λ_p		877		nm
Spectral bandwidth at 50%	I_F = 50 mA	$\Delta\lambda_{0.5}$		53		nm

Labeling

Type	Lot N°	Φ_e (typ, min, max)	Quantity
ELC-870-29-2			

Packing

Chips on adhesive film with wire-bond side on top